



## NPN BD433 – BD435 – BD437

### SILICON NPN POWER TRANSISTORS.

The BD433-BD435-BD437 are NPN Transistors mounted in Jedec TO-126 plastic package. They are recommended for use in medium power linear and switching applications. PNP complements are BD434-BD436-BD438. Compliance to RoHS.

#### ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings	Value	Unit	
$V_{CBO}$	Collector-Base Voltage ( $I_E = 0$ )	BD433	22	V
		BD435	32	
		BD437	45	
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	BD433	22	V
		BD435	32	
		BD437	45	
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	5	V	
$I_C$	Collector Current	4	A	
$I_{CM}$	Collector Current Peak	7		
$I_B$	Base Current	1	A	
$P_C$	Total power Dissipation	$T_C = 25^\circ\text{C}$ 36	W	
$T_J$	Junction Temperature	150	$^\circ\text{C}$	
$T_{Stg}$	Storage Temperature	-65 to +150	$^\circ\text{C}$	

#### THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
$R_{thJ-c}$	Thermal Resistance, Junction-Case	3.5	$^\circ\text{C}/\text{W}$
$R_{thJ-a}$	Thermal Resistance, Junction-ambient in free air	100	$^\circ\text{C}/\text{W}$

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### ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit	
$I_{CBO}$	Collector cut-off current	$I_E = 0, V_{CB} = 22\text{ V}$	BD433	-	-	100	$\mu\text{A}$
		$I_E = 0, V_{CB} = 32\text{ V}$	BD435				
		$I_E = 0, V_{CB} = 45\text{ V}$	BD437				
$I_{CES}$	Collector cut-off current	$V_{BE} = 0, V_{CE} = 22\text{ V}$	BD433	-	-	100	$\mu\text{A}$
		$V_{BE} = 0, V_{CE} = 32\text{ V}$	BD435				
		$V_{BE} = 0, V_{CE} = 45\text{ V}$	BD437				
$I_{EBO}$	Emitter cut-off current	$I_C = 0$ $V_{EB} = 5\text{ V}$	BD433	-	-	1	mA
			BD435				
			BD437				
$V_{CEO(SUS)}$	Collector-Emitter sustaining Voltage (*)	$I_B = 0$ $I_C = 100\text{ mA}$	BD433	22	-	-	V
			BD435	32	-	-	
			BD437	45	-	-	
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	$I_C = 2\text{ A}$ $I_B = 200\text{ mA}$	BD433	-	-	0.5	V
			BD435			0.6	
			BD437			0.6	
$V_{BE}$	Base-Emitter Voltage(*)	$I_C = 2\text{ A}$ $V_{CE} = 1\text{ V}$	BD433	-	-	1.1	V
			BD435			1.2	
			BD437			1.2	
$h_{FE}$	DC Current Gain (*)	$I_C = 10\text{ mA}$ $V_{CE} = 5\text{ V}$	BD433	40	-	130	-
			BD435			130	
			BD437			130	
		$I_C = 500\text{ mA}$ $V_{CE} = 1\text{ V}$	BD433	85	-	140	
			BD435			140	
			BD437			140	
		$I_C = 2\text{ A}$ $V_{CE} = 1\text{ V}$	BD433	50	-	-	
			BD435			-	
			BD437			-	
$f_T$	Transition frequency	$I_C = 250\text{ mA}$ $V_{CE} = 1\text{ V}$	BD433	3	-	-	MHz
			BD435				
			BD437				

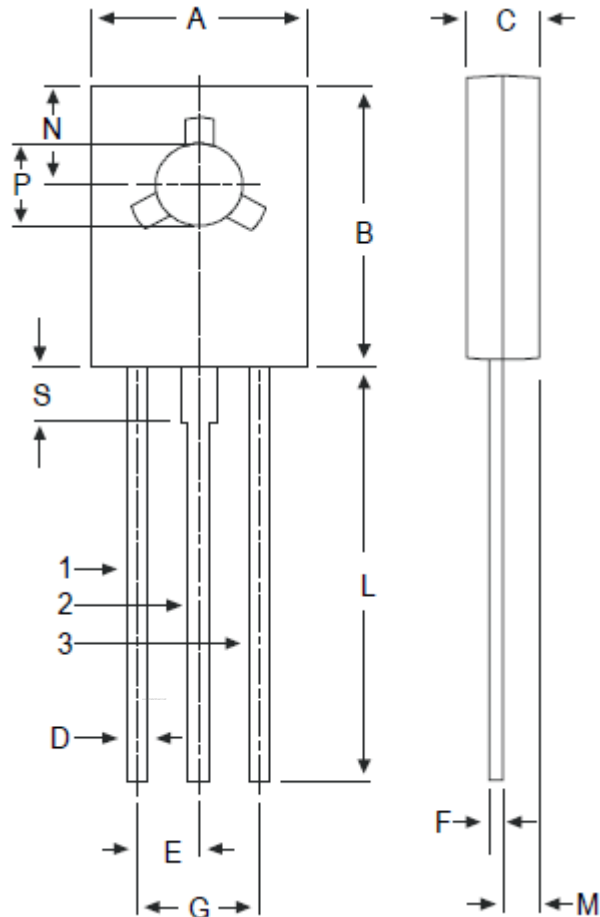
1. Measured under pulse conditions :  $t_P < 300\mu\text{s}$ ,  $\delta < 1.5$

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### MECHANICAL DATA CASE TO-126

	DIMENSIONS	
	min	max
A	7.4	7.8
B	10.5	10.8
C	2.4	2.7
D	0.7	0.9
E	2.25 typ.	
F	0.49	0.75
G	4.4 typ.	
L	15.7 typ.	
M	1.27 typ.	
N	3.75 typ.	
P	3.0	3.2
S	2.54 typ.	

Pin 1 :	Emitter
Pin 2 :	Collector
Pin 3 :	Base



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